

**AMENDMENTS TO THE SPECIFICATION**

At page 1, please delete the section entitled "TECHNICAL FIELD" (lines 6-11), and replace with the following:

**CROSS-REFERENCE TO RELATED APPLICATIONS**

This application is the U.S. National Phase filing under 35 U.S.C. §371 of PCT/JP2004/012235, filed August 19, 2004, which designated the United States and was published in English, which ~~Priority is claimed on~~ claims priority to Japanese Patent Application No. 2003-325953, filed September 18, 2003, the entire content contents of which ~~is~~ are incorporated herein by reference.

**TECHNICAL FIELD**

The present invention relates to a positive photoresist composition and to a resist pattern formation method.